

MOS FIELD EFFECT TRANSISTOR

2SK1398

N-CHANNEL MOS FET FOR HIGH SPEED SWITCHING

* DESCRIPTION

The 2SK1398 is N-channel MOS Field Effect Transistor designed for a high-speed switching device in digital circuits. The 2SK1398 is driven by a 2.5-V power source, it is suitable for applications including headphone stereos which need power saving.

ORDERING INFORMATION

PART NUMBER	PACKAGE		
2SK1398	SST		

FEATURES

- Directly driven by ICs having a 3-V power supply.
- Not necessary to consider driving current because of its high input impedance.
- Possible to reduce the number of parts by omitting the bias resistor.
- Can be used complementary with the 2SJ184.

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vgs= 0 V)	VDSS	50	V
Gate to Source Voltage (Vbs= 0 V)	Vgss	±7.0	V
Drain Current (DC)	ID(DC)	±100	mA
Drain Current (pulse) Note	ID(pulse)	±200	mA
Total Power Dissipation	Рт	250	mW
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Note PW \leq 10 ms, Duty cycle \leq 50 %

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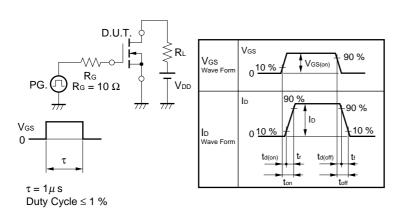
Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.



ELECTRICAL CHARACTERISTICS (TA = 25 °C)

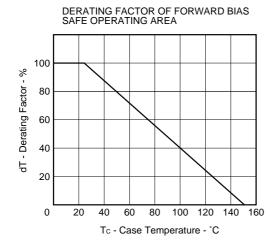
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain Cut-off Current	Ipss	V _{DS} = 50 V, V _{GS} = 0 V			10	μΑ
Gate Leakage Current	Igss	Vgs = ±7.0 V, Vps = 0 V			±5.0	μΑ
Gate to Source Cut-off Voltage	V _{GS(off)}	$V_{DS} = 3.0 \text{ V}, I_{D} = 1.0 \ \mu\text{A}$	0.9	1.2	1.5	٧
Forward Transfer Admittance	yfs	V _{DS} = 3.0 V, I _D = 10 mA	20	38		mS
Drain to Source On-state Resistance	RDS(on)1	V _G S = 2.5 V, I _D = 10 mA		22	40	Ω
	RDS(on)2	V _G S = 4.0 V, I _D = 10 mA		14	20	Ω
Input Capacitance	Ciss	V _{DS} = 3.0 V		8		pF
Output Capacitance	Coss	Vgs = 0 V		7		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		3		pF
Turn-on Delay Time	td(on)	V _{DD} = 3.0 V		15		ns
Rise Time	tr	lo = 20 mA		100		ns
Turn-off Delay Time	td(off)	V _{GS(on)} = 3.0 V		30		ns
Fall Time	tf	$R_G = 10 \Omega$, $R_L = 150 \Omega$		35		ns

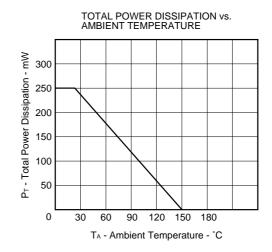
TEST CIRCUIT SWITCHING TIME

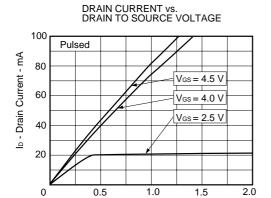




TYPICAL CHARACTERISTICS (TA = 25 °C)

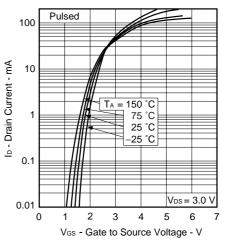


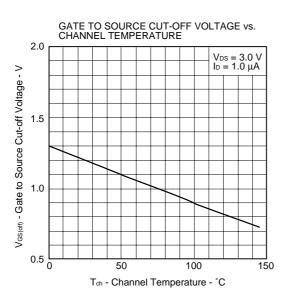




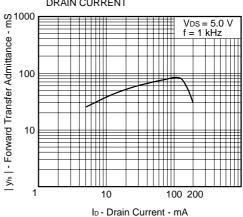
V_{DS} - Drain to Source Voltage - V





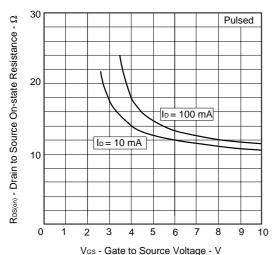


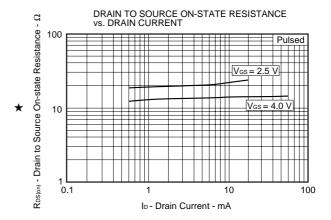


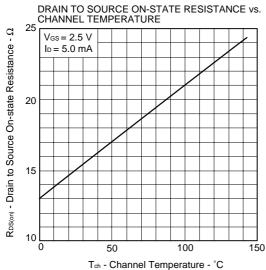


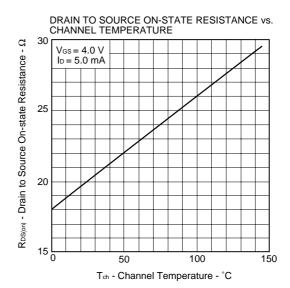
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DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

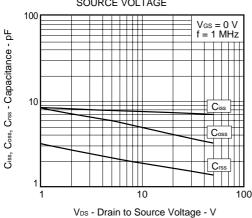


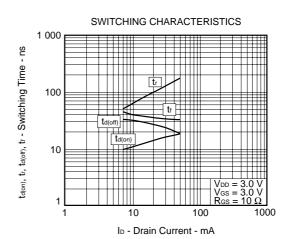






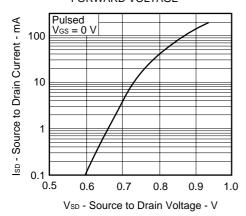
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE





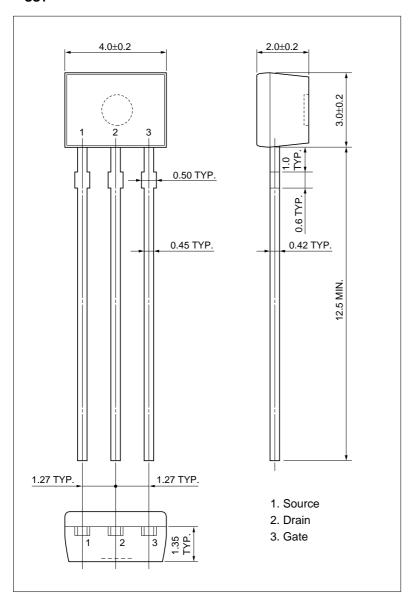


SOURCE TO DRAIN DIODE FORWARD VOLTAGE

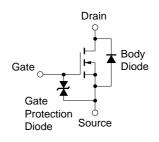


PACKAGE DRAWING (Unit: mm)

SST



EQUIVALENT CIRCUIT



Marking: G25

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

[MEMO]

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